TOSHIBA Field Effect Transistor Silicon N Channel Junction Type

2SK369

For Low Noise Audio Amplifier Applications

- Suitable for use as first stage for equalizer and MC head amplifiers.
- High $|Y_{fs}|$: $|Y_{fs}| = 40 \text{ mS}$ (typ.) (VDS = 10 V, VGS = 0, IDSS = 5 mA)
- High breakdown voltage: $V_{GDS} = -40 V (min)$
- Super low noise: NF = 1.0dB (typ.)

 $(V_{DS} = 10 \text{ V}, \text{ I}_{D} = 5 \text{ mA}, \text{ f} = 1 \text{ kHz}, \text{ R}_{G} = 100 \Omega)$

• High input impedance: $I_{GSS} = -1 nA (max) (V_{GS} = -30 V)$

Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Gate-drain voltage	V _{GDS}	-40	V
Gate current	lG	10	mA
Drain power dissipation	PD	400	mW
Junction temperature	Tj	125	°C
Storage temperature range	T _{stg}	-55~125	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the

Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate cut-off current	I _{GSS}	$V_{GS} = -30 \text{ V}, V_{DS} = 0$	_	_	-1.0	nA
Gate-drain breakdown voltage	V (BR) GDS	$V_{DS}=0,\ I_G=-100\ \mu A$	-40		_	V
Drain current	I _{DSS} (Note 1)	$V_{DS} = 10 \text{ V}, \text{ V}_{GS} = 0$	5.0		30	mA
Gate-source cut-off voltage	V _{GS (OFF)}	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 0.1 \mu\text{A}$	-0.3	_	-1.2	V
Forward transfer admittance	Y _{fs}	$\label{eq:VDS} \begin{array}{l} V_{DS} = 10 \text{ V}, V_{GS} = 0, f = 1 \text{kHz}, \\ (\text{I}_{DSS} = 5 \text{mA}) \end{array}$	25	40		mS
Input capacitance	C _{iss}	$V_{DS} = 10 \text{ V}, \text{ V}_{GS} = 0, \text{ f} = 1 \text{ MHz}$	_	75		pF
Reverse transfer capacitance	C _{rss}	$V_{GD} = -10 V, I_D = 0, f = 1 MHz$	_	15		pF
Noise figure (Note 2) –	NF (1)	$V_{DS} = 10 \text{ V}, \text{ R}_{G} = 100 \ \Omega, \text{ I}_{D} = 5 \text{ mA}, \text{ f} = 100 \text{ Hz}$	_	5	10	dB
	NF (2)	V_{DS} = 10 V, R_G = 100 $\Omega,$ I_D = 5 mA, f = 1 kHz		1	2	

Note 1: I_{DSS} classification GR: 5.0~10.0 mA, BL: 8.0~16.0 mA, V: 14.0~30.0 mA

Note 2: Use this in the low voltage region (VDS < 15 V) for low noise applications.



4.7 MAX

12.7 MIN.

0.8

1.27

TO-92

SC-43

2-5F1D

I MAX.

5.1 MAX

2 3

DRAIN
 GATE
 SOURCE

0.4

0.4

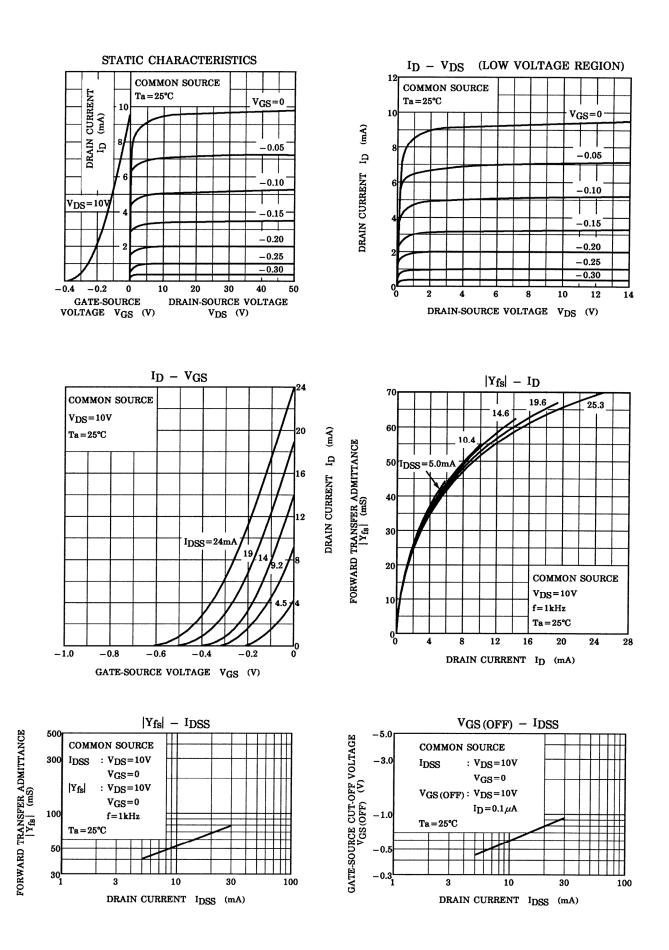
0.55 MAX

JEDEC

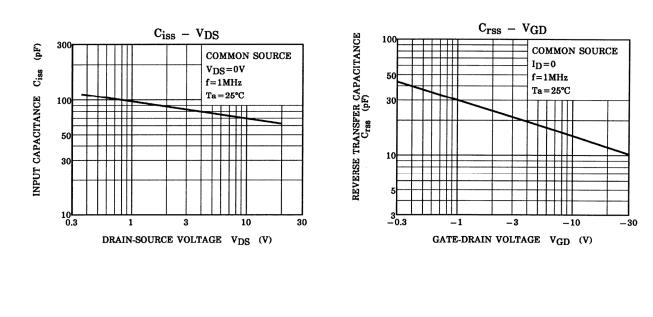
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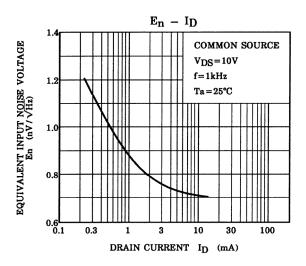
TOSHIBA

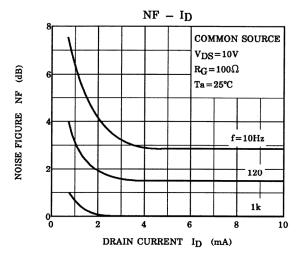
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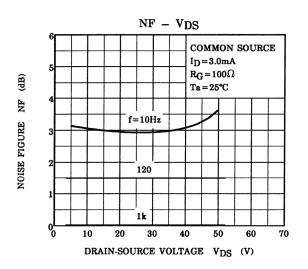


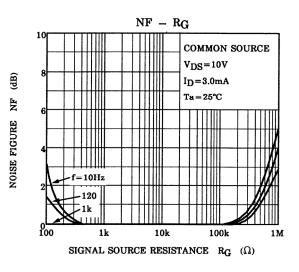
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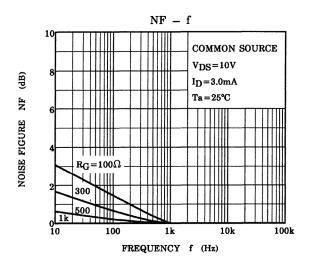


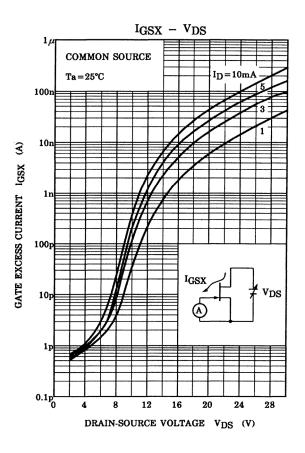


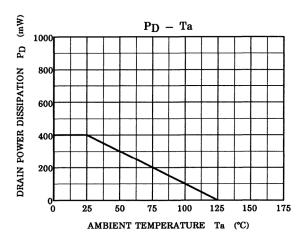




TOSHIBA







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20070701-EN GENERAL

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